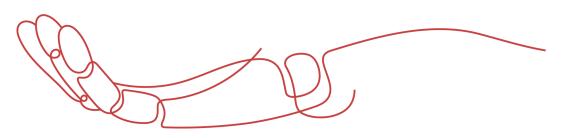


# **PRODUCT DATA SHEET**



To learn more about JGSEMI, please visit our website at







Datasheet

Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to Fairchild\_questions@jgsemi.com.



### **Bi-directional ESD Protection Diode in DFN1006 Package**

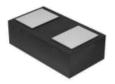
#### **Features**

Capacitance: 15pF(typ.)Reverse Working Voltage: 5V

■ IEC 61000-4-2 (ESD Air): ±25KV IEC 61000-4-2 (ESD Contact): ±25KV IEC 61000-4-5 (Lightning 8/20µs): 8A

### **Pin Description**

**Schematic Diagram** 



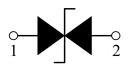
### **Applications**

■ Smart Phone and Tablet PC

■ TV and Set Top Box

■ Wearable Devices

■ PDA



### Limiting Values( $T_A = 25$ °C, unless otherwise specified)

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>ESD</sub>	Electrostatic Discharge Voltage	IEC 61000-4-2; Contact Discharge	-	±25	kV
		IEC 61000-4-2; Air Discharge	-	±25	kV
$P_{PP}$	Peak Pulse Power	t <sub>P</sub> = 8/20 μs	-	80	W
I <sub>PPM</sub>	Rated Peak Pulse Current	t <sub>P</sub> = 8/20 μs	-	8	Α
TA	Ambient Temperature Range	-	-55	125	°C
T <sub>stg</sub>	Storage Temperature Range	-	-55	150	°C

## Electrical Characteristics(T<sub>A</sub> = 25 °C, unless otherwise specified)

Symbol	Parameter	Conditions	Min	Тур.	Max	Unit
$V_{RWM}$	Reverse Working Voltage	T <sub>A</sub> = 25 °C	_	-	5.0	V
$V_{BR}$	Breakdown Voltage	I <sub>R</sub> = 1mA; T <sub>A</sub> = 25 °C	5.6	6.5	8.4	V
I <sub>R</sub>	Reverse Leakage Current	V <sub>RWM</sub> = 5V; T <sub>A</sub> = 25 °C	-	-	0.1	μA
Vc	Clamping Voltage	I <sub>PP</sub> =8A, t <sub>P</sub> =8/20μs	-	-	10	V
Сл	Junction Capacitance	V <sub>R</sub> = 0V, f = 1 MHz	-	15	18	pF



### **Typical Characteristics**

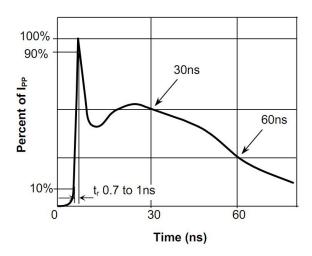


Fig.1 Pulse Waveform-ESD(IEC61000-4-2)

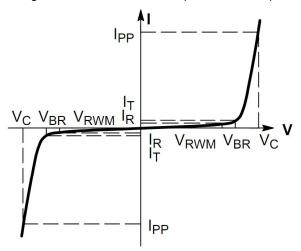


Fig.3 V-I Characteristics for Bidirectional Diode

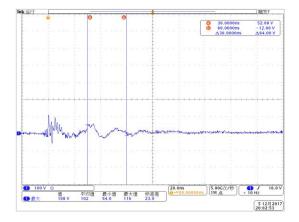


Fig.5 Clamping Voltage at IEC61000-4-2 +8kV Pulse Waveform

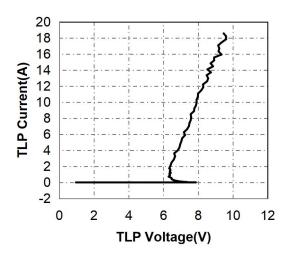


Fig.2 Transmission Line Pulse (TLP)

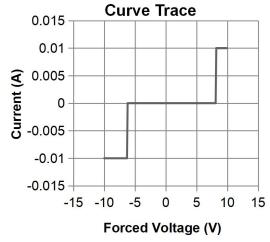


Fig.4 IV Curve

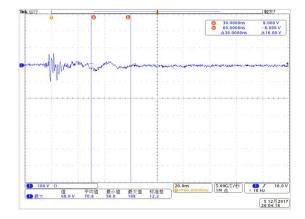
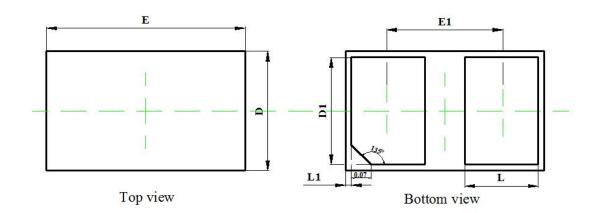


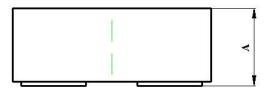
Fig.6 Clamping Voltage at IEC61000-4-2
-8kV Pulse Waveform



## **Package Outline Dimensions**

### **DFN1006 Package Outline**



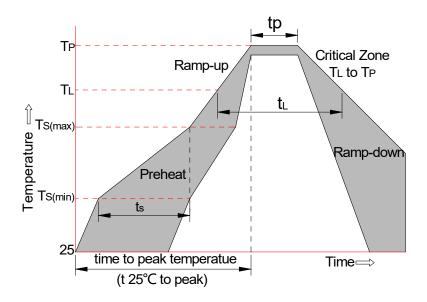


Side view

Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.320	0.420	0.013	0.017	
D	0.550	0.650	0.022	0.026	
E	0.950	1.050	0.037	0.041	
D1	0.450	0.550	0.018	0.022	
E1	0.550	0.650	0.022	0.026	
L	0.280	0.380	0.011	0.015	
L1	0.000	0.100	0.000	0.004	



### **Soldering Parameters**



Reflow Condition		Pb-Free Assembly		
Pre-heat	-Temperature Min (T <sub>s(min)</sub> )	+150°C		
	-Temperature Max(T <sub>s(max)</sub> )	+200°C		
	-Time (Min to Max) (ts)	60-180 secs.		
Average ramp up rate (Liquid us Temp (T <sub>L</sub> ) to peak)		3°C/sec. Max		
$T_{s(max)}$ to $T_L$ - Ramp-up Rate		3°C/sec. Max		
Reflow	-Temperature(T <sub>L</sub> )(Liquid us)	+217°C		
	-Temperature(t <sub>L</sub> )	60-150 secs.		
Peak Temp (T <sub>p</sub> )		+260(+0/-5)°C		
Time within 5°C of actual Peak Temp (tp)		30 secs. Max		
Ramp-down Rate		6°C/sec. Max		
xTime 25°C to Peak Temp (T <sub>P</sub> )		8 min. Max		
Do not exceed		+260°C		



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